



TET ESTEL AS
ESTONIA

May
2013

Series
TF271-200

Fast Stud Mounted Thyristor
Type TF271-200

Low on-state and switching losses
Low reverse recovery charge
Center amplifying gate

Maximum mean on-state current	I_{TAV}	200 A							
Maximum repetitive peak off-state and reverse voltage	U_{DRM} U_{RRM}	600 ÷ 1400 V							
Turn-off time	t_q	25; 32; 40 μs							
U_{DRM}, U_{RRM}, V	600	700	800	900	1000	1100	1200	1300	1400
Voltage code	6	7	8	9	10	11	12	13	14
$T_{vj}, ^\circ C$	- 60 ÷ 125								

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	TF271-200	Conditions
I_{TAV}	Mean on-state current	A	200	$T_c=90^\circ C$, 180° half-sine wave, 50 Hz
I_{TRMS}	RMS on-state current	A	314	$T_c=90^\circ C$
I_{TSM}	Surge on-state current	kA	6,0 6,3	$T_{vj}=125^\circ C$ $T_{vj}=25^\circ C$ tp=10 ms $U_R=0$
I^2t	Limiting load integral	kA^2s	180 198	$T_{vj}=125^\circ C$ $T_{vj}=25^\circ C$
U_{DRM}, U_{RRM}	Repetitive peak off-state and reverse voltage	V	600÷1400	$T_j \min \leq T_{vj} \leq T_{jM}$ 180° half-sine wave, 50 Hz Gate open
U_{DSM}, U_{RSM}	Non-repetitive peak off-state and reverse voltage	V	660÷1500	$T_j \min \leq T_{vj} \leq T_{jM}$ 180° half-sine wave tp=10 ms, Single pulse Gate open
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current : non - repetitive repetitive	A/ μ s	1000 400	$T_{vj}=125^\circ C$; $U_D=0,67 U_{DRM}$, Gate pulse : 10V,5 Ω , 1 μ s rise time, 10 μ s
U_{RGM}	Peak reverse gate voltage	V	5	$T_j \min \leq T_{vj} \leq T_{jM}$
T_{stg}	Storage temperature	$^\circ C$	-60÷80	
T_{vj}	Junction temperature	$^\circ C$	-60÷125	

CHARACTERISTICS

U_{TM}	Peak on-state voltage	V	2,2	$T_{vj}=25^\circ C$, $I_{TM}=3,14 I_{TAV}$
$U_{T(To)}$	Threshold voltage	V	1,38	$T_{vj}=125^\circ C$
R_T	On-state slope resistance	m Ω	1,50	1,57 $I_{TAV} < I_T < 4,71 I_{TAV}$
I_{DRM} I_{RRM}	Repetitive peak off-state and reverse current	mA	35 35	$T_{vj}=125^\circ C$, $U_D = U_{DRM}$ $U_R = U_{RRM}$

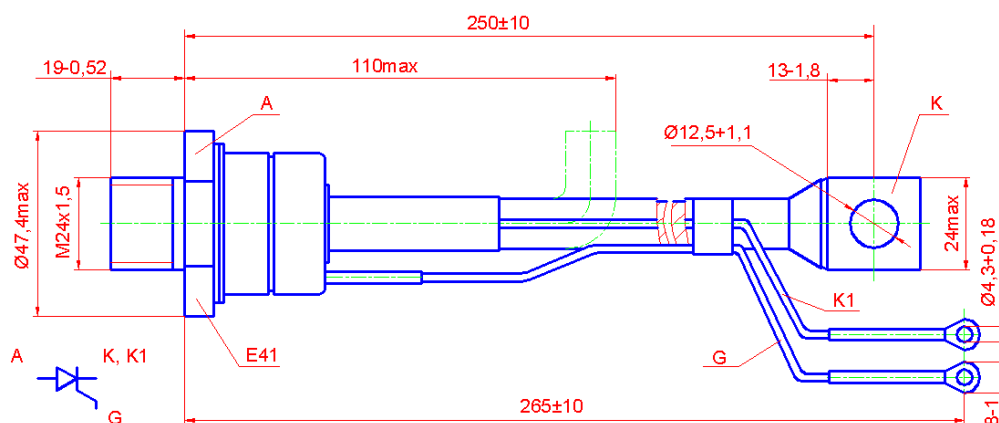
CHARACTERISTICS

Symbols and parameters		Units	TF271-200	Conditions
I_L	Latching current	A	1	$T_{vj}=25^{\circ}\text{C}, U_D=12\text{V}$ Gate pulse : 10V, 5 Ω , 1 μs rise time, 10 μs
I_H	Holding current	A	0,3	$T_{vj}=25^{\circ}\text{C}, U_D=12\text{V}$, Gate open
U_{GT}	Gate trigger direct voltage	V	2,5 5,0	$T_{vj}=25^{\circ}\text{C}$, $T_{vj}=-60^{\circ}\text{C}$
I_{GT}	Gate trigger direct current	A	0,3 0,85	$T_{vj}=25^{\circ}\text{C}$, $T_{vj}=-60^{\circ}\text{C}$
U_{GD}	Gate non-trigger direct voltage	V	0,25	$T_{vj}=125^{\circ}\text{C}$, $U_D = 0,67 U_{DRM}$
I_{GD}	Gate non-trigger direct current	mA	10	Direct gate current
t_{gd}	Delay time	μs	1,9	$T_{vj}=25^{\circ}\text{C}, U_D=500\text{V}$ $I_{TM} = 200 \text{ A}$
t_{gt}	Turn-on time	μs	3,2	Gate pulse : 10V, 5 Ω , 1 μs rise time, 10 μs
t_q	Turn-off time	μs	25 \div 40 32 \div 50	$T_{vj}=125^{\circ}\text{C}$, $I_{TM}=200 \text{ A}$ $di_R/dt = 10 \text{ A}/\mu\text{s}$, $U_R=100\text{V}$ $U_D = 0,67 U_{DRM}$ $du_D/dt=50 \text{ V}/\mu\text{s}$ $du_D/dt=200 \text{ V}/\mu\text{s}$
Q_{rr}	Recovered charge	μC	240	$T_{vj}=125^{\circ}\text{C}$, $I_{TM}=200 \text{ A}$ $di_R/dt = 50 \text{ A}/\mu\text{s}$, $U_R=100\text{V}$
t_{rr}	Reverse recovery time	μs	3,2	
I_{rrM}	Peak reverse recovery current	A	150	
$(du_D/dt)_{crit}$	Critical rate of rise of off-state voltage	V/ μs	500 1000	$T_{vj}=125^{\circ}\text{C}$, $U_D = 0,67 U_{DRM}$ Gate open
R_{thjc}	Thermal resistance junction to case	$^{\circ}\text{C}/\text{W}$	0,075	Direct current

ORDERING

	TF	271	200	14	6	4	2	
	1	2	3	4	5	6	7	

1. Fast thyristor.
2. Design version.
3. Mean on-state current, A.
4. Voltage code (14=1400 V).
5. Critical rate of rise of off-state voltage ($6 \geq 500 \text{ V}/\mu\text{s}$, $7 \geq 1000 \text{ V}/\mu\text{s}$).
6. Group of turn-off time ($du_D/dt=50 \text{ V}/\mu\text{s}$, $3 \leq 40 \mu\text{s}$, $4 \leq 32 \mu\text{s}$, $5 \leq 25 \mu\text{s}$).
7. Group of turn-on time ($2 \leq 3,2 \mu\text{s}$).



Tightening torque : 40 \div 60 Nm
Weight : 480 grams

